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(54) Low noise-high linearity HEMT-HBT composite

(57) 4-terminal HEMT-HBT composite devices, based upon monolithically integrated HEMT-HBT technology and configured in various topologies, are useful in a wide range of applications which currently utilize discrete MMICs. In particular, the 4-terminal topologies are easily configured as 3-terminal composite devices useful in various 2-port and 3-port MMIC circuit applications, such as low noise-high linearity amplifiers as well as mixers, which provide the benefits of a reduction in size, as well as corresponding cost while providing better performance than utilizing either HEMT or HBT devices individually.

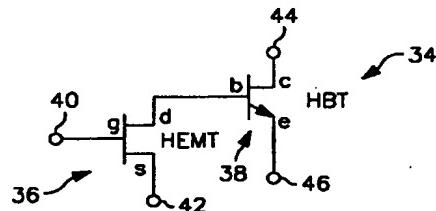


FIG. IA

Description**BACKGROUND OF THE INVENTION**5 **1. Field of the Invention**

The present invention relates to monolithic microwave integrated circuits (MMICs) and more particularly to low noise-high linearity MMICs formed from monolithically integrated high-electron mobility transistor (HEMT) and heterojunction bipolar transistor (HBT) devices configured in various topologies, useful in a wide range of applications, which reduce the size, cost, as well as power consumption of such applications while providing relatively better overall performance capability than utilizing either HEMT or HBT devices individually.

15 **2. Description of the Prior Art**

Various applications are known in which low noise and high linearity performance is required. Examples of such applications include low noise amplifiers (LNAs), variable gain amplifiers (VGAs), transmit/receive (T/R) modules, power amplifiers, transimpedance amplifiers and optical receivers used in various products including wireless products, cellular telephony, fiber optic data links, portable electronics and the like. In many of such applications, it is known to utilize a high-electron mobility transistor (HEMT) for its low-noise figure performance and a heterojunction bipolar transistor (HBT) for its high-linearity performance. Because of the limited topologies available in known monolithic microwave integrated circuits (MMICs), oftentimes, separate MMICs are used. In certain applications, for example, in applications where there are space constraints, the use of multiple MMICs is undesirable. In addition, the use of multiple MMICs increases the cost as well as the complexity and power consumption of the system in which such devices are used.

25 MMICs have been developed in which HEMT and HBT technologies have been monolithically integrated in a single MMIC, for example, as disclosed in copending U.S. Patent Application Serial No. 08/333,538, filed November 2, 1994, hereby incorporated by reference. However, the topologies of such integrated HEMT-HBT MMICs are limited. While such MMICs are useful in certain applications, many applications as discussed above require different circuit configurations and thus in such applications, separate HEMT and HBT MMICs are used. As discussed above, the use of multiple MMICs increases the cost, as well as the complexity of the circuitry and is relatively limited in applications having size constraints.

SUMMARY OF THE INVENTION

35 It is an object of the present invention to solve various problems in the prior art.

It is yet another object of the present invention to provide microwave monolithic integrated circuits (MMICs) with integrated HEMT-HBT devices configured in various topologies that are useful in a wide range of applications.

Briefly, the present invention relates to a 4-terminal MMIC formed from monolithically integrated HEMT-HBT technology in various topologies useful in a wide range of applications which currently utilize multiple discrete MMICs. In particular, the 4-terminal topologies are easily configured as 3-terminal devices by grounding one of the terminals. The 3-terminal devices can easily be configured in various two-port and three-port configurations useful in various applications in which multiple MMICs are known to be used, such as low noise-high linearity amplifiers as well as mixers, which provide the benefits of a reduction in size, cost, as well as lower power consumption while providing better performance than either HEMT or HBT devices individually.

45 **BRIEF DESCRIPTION OF THE DRAWING**

These and other advantages of the present invention will become apparent with reference to the following specification and attached drawing, wherein:

50 FIGS. 1a-1b are schematic representations of two HEMT-HBT 4-terminal composite devices illustrating two topologies in accordance with the present invention;

FIG. 2 is a schematic representation of a low noise-high linearity HEMT common-gate HBT common-emitter 3-terminal composite device in accordance with the present invention;

55 FIG. 3 is a schematic diagram of a low noise-high linearity HEMT common-gate HBT common-collector 3-terminal composite device in accordance with the present invention;

FIG. 4 is a schematic diagram of a low noise-high linearity HEMT common-source HBT common-emitter 3-terminal composite device in accordance with the present invention;

FIG. 5 is a schematic diagram of a low noise-high linearity HEMT common-source HBT common-collector 3-termi-

nal composite device in accordance with the present invention;

FIG. 6 is a schematic diagram of a low noise-high linearity HEMT common-source HBT common-base 3-terminal composite device in accordance with the present invention;

FIG. 7 is a schematic diagram of a low noise-high linearity HEMT common-source HBT 3-terminal mixer device in accordance with the present invention;

FIG. 8 is a schematic diagram of a HEMT actively matched HBT Darlington amplifier in accordance with the present invention;

FIG. 9 is a graphical representation of the gain and input return loss of the HEMT-HBT amplifier illustrated in FIG. 8 for various HEMT biasing levels as a function of frequency;

FIG. 10 is a graphical representation of the noise figure performance of the HEMT-HBT amplifier illustrated in FIG. 8 as a function of DC bias of the HEMT;

FIG. 11 is a graphical illustration of the IP3 performance of the HEMT-HBT amplifier illustrated in FIG. 8 for three different HEMT DC bias voltages;

FIG. 12 is a schematic diagram of a common-source HEMT-HBT Darlington amplifier in accordance with the present invention;

FIG. 13 is a graphical illustration of the gain and return loss performance of the HEMT-HBT amplifier illustrated in FIG. 12 as a function of frequency;

FIG. 14 is a graphical illustration of the noise figure and IP3 performance of the HEMT-HBT Darlington amplifier illustrated in FIG. 12 as a function of frequency; and

FIG. 15 is a graphical illustration of the gain and output power as a function of input power of the HEMT-HBT Darlington amplifier illustrated in FIG. 12.

DETAILED DESCRIPTION OF THE INVENTION

As mentioned above, low noise and high linearity performance is required in a relatively wide range of applications. In order to achieve such performance objectives, high-electron mobility transistors (HEMTs) and heterojunction bipolar transistor (HBT) devices are known to be used for such applications. Other than a relatively few topologies formed as monolithic microwave integrated circuits (MMIC) in which the HEMT and HBT technologies are integrated, many known low noise and high linearity performance applications are known to use separate HEMT and HBT MMICs. The present invention provides HEMT-HBT composite device topologies that combine key performance and device properties in order to provide advantages in size, performance and circuit functionality.

The performance capabilities of the HEMT device technology, HBT device technology and composite HEMT-HBT devices in accordance with the present invention is illustrated in Table 1.

TABLE 1

Device & Technology	Gm	Noise Figure	IP3 (Linearity)	Power Efficiency	Frequency Capability
HBT	High	Medium	High	High	dc->20 GHz
HEMT	High	Low	Medium	Medium	dc->100 GHz
HEMT-HBT Composite devices (general)	Very High $\approx Gm_{hemt} * Gm_{hbt}$	Low	High	High	dc->20 GHz
HEMT-HBT Topology (FIG. 2) CG-CE	Very High $\approx Gm_{hemt} * Gm_{hbt}$	Medium	High	High	dc->20 GHz
HEMT-HBT Topology (FIG. 4) CS-CE	Very High $\approx Gm_{hemt} * Gm_{hbt}$	Low	High	High	dc->20 GHz
HEMT-HBT Topology (FIG. 6) CS-CB	High $\approx Gm_{hemt}$	Low	High	High	dc->20 GHz

As illustrated in Table 1, the overall capability of the HEMT-HBT composite devices in accordance with the present invention provide a combination of low noise and high linearity characteristics, which cannot be obtained from either the HEMT or HBT devices alone. In addition, the HEMT-HBT monolithic composite devices can provide better performance than obtainable from an equivalent discrete hybrid (MIC) implementation of the same composite device topologies.

The topologies for the composite HEMT-HBT devices in accordance with the present invention are illustrated in FIGS. 1a and 1b. As shown, each of the two topologies is configured as a 4-terminal device and includes a low noise

HEMT device that is directly coupled to a high linearity HBT device. Each of the terminals are defined by an open circle. By directly coupling the HEMT and HBT, the composite devices will maintain low noise figure characteristics of the HEMT and the high linearity characteristics of the HBT. In order to provide a relatively wide range of applications, each of the topologies are configured with four terminals to enable the topologies to apply in a relatively wide range of circuit applications, including various amplifiers and mixers as discussed below.

The two 4-terminal topologies are shown with electrical coupling to terminals for connection to external circuits. These terminals are defined by an open circle. As discussed below, one of the terminals can be grounded and eliminated to form 3-terminal devices and 2-port and 3-port circuit networks as discussed below.

The first topology is generally identified with the reference numeral 34. The composite device 34 includes a HEMT 36 and an HBT 38. In the composite device 34, the drain electrode of the HEMT is directly connected to the base electrode of the HBT 38. The gate and source electrodes of the HEMT 36 are connected to external terminals 40 and 42, while the collector and emitter electrodes of the HBT 38 are connected to external terminals 44 and 46, respectively.

A second 4-terminal topology of a composite HEMT-HBT device is illustrated in FIG. 1b and generally identified with the reference numeral 48. The composite device 48 includes a HEMT 50 and an HBT 52. In this topology, the drain electrode of the HEMT 50 is directly connected to the emitter electrode of the HBT 52. The gate and source electrodes of the HEMT 50 are connected to external terminals 54 and 56, respectively, while the base and collector electrodes of the HBT 52 are connected to external terminals 58 and 60, respectively, to form the 4-terminal HEMT-HBT composite device 48.

As shown in FIGS. 2-7, the 4-terminal topologies, illustrated in FIGS. 1a and 1b, can be configured as 3-terminal devices which can be used as a basis for various useful 2- and 3-port circuit configurations. For example, the composite HEMT-HBT device 34, illustrated in FIG. 1a, can be converted into a useful 3-terminal device configured as a 2-port circuit 62 for low noise-high linearity amplification applications. In this application like reference numerals are used to identify like components and open circles are used to define the composite device terminals. As shown in FIG. 2, the external terminal 40, connected to the source electrode of the HEMT 36, is used as an input terminal, while the external terminal 44, connected to the collector electrode of the HBT 38, is used as an output terminal. The emitter electrode of the HBT 38 is the third terminal as defined by the open circle. In the composite HEMT-HBT device 62, illustrated in FIG. 2, the external terminal 42 of the 4-terminal device defined in FIG. 1a from the gate electrode of the HEMT 36 is grounded and thereby eliminated to form a 3-terminal composite device configuration. In order to provide a useful 2-port circuit configuration for use in low noise-high linearity amplification applications, the emitter electrode of the HBT 38 is connected to ground by way of an external emitter resistor 64. An external load resistor R_L 66 may be connected between ground and an external terminal 68 to define a load impedance for the 2-port output. The low noise-high linearity HEMT common-gate HBT common-emitter 3-terminal composite device is thus used to construct a 2-port low noise-high linearity amplifier 62.

The HEMT-HBT topology, illustrated in FIG. 1a, can also be configured as a useful 3-terminal device employed in a 2-port low noise-high linearity circuit 70 as illustrated in FIG. 3. In the 2-port circuit 70, the gate electrode of the HEMT 36 is connected to ground. The collector electrode of the HBT 38 is defined as a terminal 44 of the 3-terminal composite device and is designated with an open circle. In order to provide a useful configuration for low noise-high linearity amplifiers applications, an external load resistor R_L 72 may be connected between ground and an output terminal 74 to define a load impedance at the output of the amplifier. The emitter electrode of the HBT 38, connected to the terminal 46, defines the output of the device to form a low noise-high linearity HEMT common-gate HBT common-collector 3-terminal composite device whereby the collector of the HBT 38 is the third terminal and is coupled to ground to form a useful 2-port amplifier.

An important aspect of the 2-port amplifier circuit configurations, illustrated in FIGS. 2 and 3, is that a relatively low noise common-gate HEMT may be used to actively match the input of the amplifier without the use of a relatively large area consuming microstrip or lumped element components. As such, the composite devices 62 and 70 can be directly coupled to an external circuit. By implementing the HBT 24 in a common-emitter configuration, the composite device 62, illustrated in FIG. 2 will have a relatively large transconductance and high-output impedance, useful for high voltage gain applications using feedback topologies.

The composite device 70, illustrated in FIG. 3, is configured as a HEMT common-gate HBT common-collector device. By employing the HBT in a common-collector configuration, the resulting HEMT-HBT composite device will have a relatively low output impedance and thus be suitable for driving low impedance systems. In both of the amplifier configurations illustrated in FIGS. 2 and 3, a common-gate HEMT input device allows the noise figure or input return-loss to be electronically tuned, for example, as disclosed in "A Monolithic HEMT-HBT Direct Coupled Amplifier with Active Input Match," by K.W. Kobayashi, D.C. Streit, D.K. Umemoto, T.R. Block and A.K. Oki, *IEEE Microwave & Guided-Wave Letters*, Vol. 6, No. 1, January 1996, pp. 55-57, hereby incorporated by reference.

The effective transconductance of the common-emitter HBT composite device 62, illustrated in FIG. 2, is given in equation (1):

$$Gm_{eff} \approx \left\{ \frac{Gm_{HEMT}}{1 + Gm_{HEMT} * r_s} * r_{ds} \right\} \left\{ \frac{\alpha_0}{\frac{r_b}{\beta_0+1} + \frac{1}{Gm_{HBT}} + r_e + R_e} \right\} \quad (1)$$

5

where Gm_{HEMT} is the DC transconductance, r_s is the parasitic source resistance, r_{ds} is the DC output resistance, R_e is the external emitter resistance, r_e is the dynamic emitter resistance, r_b is the base resistance, α_0 is the current gain from emitter to collector, β_0 is low-frequency forward current gain, and Gm_{HBT} is the DC transconductance of the HBT.

10 The input impedance Z_{in} of the device 62 is provided by equation (2):

$$Z_{in}(s) \approx r_s + \frac{1}{Gm_{HEMT}} \quad (2)$$

15

The output impedance Z_{out} of the device 62 is provided by equation (3):

$$Z_{out}(s) \approx r_0 * (1 + \frac{Gm_{HBT}}{1 + Gm_{HBT} * r_e}) \quad (3)$$

20

where

$$25 Gm_{HBT} + \frac{I_c * q}{n * K * T} \text{ and } \alpha_0 = \frac{\beta_0}{1 + \beta_0}$$

where r_0 is output resistance, I_c is the collector current, q is electronic charge, n is the ideality factor, K is Bortzmann's constant, and T is temperature in degrees kelvin.

30 The effective transconductance for the HEMT common-gate HBT common-collector device 70, illustrated in FIG. 3, is given by equation (4):

$$35 Gm_{eff} \approx \left\{ \frac{Gm_{HEMT}}{1 + Gm_{HEMT} * r_s} * r_{ds} \right\} \left\{ \frac{1}{\frac{r_b}{\beta_0+1} + \frac{1}{Gm_{HBT}} + r_e + R_L} \right\} \quad (4)$$

The input impedance of the HEMT common-gate HBT common-collector 3-terminal composite device 70 is given in 40 equation (5):

$$45 Z_{in}(s) \approx r_s + \frac{1}{Gm_{HEMT}} \quad (5)$$

45

while the output impedance of the device 70 is given in equation (6):

$$50 Z_{out}(s) \approx (r_e + \frac{1}{Gm_{HBT}} + \frac{r_b + r_{ds}}{\beta_0 + 1}) \quad (6)$$

The topology illustrated in FIG. 1a for the HEMT-HBT 4-terminal composite device 34 can be configured into two different 3-terminal devices, which can also be used for low noise-high linearity amplification, for example as shown in FIGS. 4 and 5. An important aspect of the 3-terminal devices configured in 2-port amplifier configurations, illustrated in 55 FIGS. 4 and 5, is that the relatively low noise common-source HEMT provides a high input impedance, which allows for the construction of low loss matching networks for tuning the input transistor for noise and bandwidth, for example in a distributed amplifier topology. With reference to FIGS. 4 and 5, like reference numerals are used to describe components having similar functions relative to the composite device 34 illustrated in FIG. 1a.

Referring to FIG. 4, a low noise HEMT common-source HBT common-emitter composite device whose terminals

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are defined by the open circles is employed as a 2-port amplifier 76. In this application, the source electrode of the HEMT 36 is connected to ground. The emitter electrode, defined as one of the 3-terminals of the composite device topology, is grounded by way of an external emitter resistor r_e 78 in order to provide a useful 2-port circuit configuration for low noise-high linearity amplifiers. The HEMT common-source configuration where the source electrode is grounded enables the output terminal 42 shown in FIG. 1b, to be eliminated. An external load resistor R_L 80 may be connected between ground and an output terminal 82 to define a load impedance at the output of the amplifier. The configuration of the HEMT-HBT 2-port amplifier as illustrated in FIG. 4 provides optimum noise figure performance in conjunction with a high-linearity HBT common emitter output.

The topology illustrated in FIG. 1a may also be used to form a HEMT common-source HBT common-collector low noise-high linearity composite device 84, illustrated in FIG. 5. In this application the source electrode of the HEMT 36 is connected to ground, thus eliminating terminal 42, illustrated in FIG. 1a. In the composite device 84, the collector electrode of the HBT 38, connected to terminal 44 of the composite device, may also be connected to ground externally. In order to provide a useful configuration, a load resistor R_L 88 may be connected between an external terminal 86 and ground to define an output load impedance for the resulting HEMT-HBT 2-port network 84.

An important aspect of the 3-terminal composite device configurations, illustrated in FIGS. 4 and 5, is that a low noise common-source HEMT provides a high-input impedance, useful in low loss matching networks to tune the input transistor for noise and bandwidth, such as in a distributed amplifier topology. In particular, a common-source HEMT input provides the best noise figure performance. The high-input impedance also allows optimal use of parallel feedback to the gate input, as well as for transimpedance amplifier applications that require a relatively high input impedance. By implementing the HBT 38 in a common-emitter configuration, the composite device 76, illustrated in FIG. 4, will have a relatively large transconductance and a relatively high output impedance, useful for high voltage gain applications using feedback topologies.

The common-collector configuration for the HBT 38 and the HEMT-HBT composite 3-port composite device 84, illustrated in FIG. 5, provides for a relatively low output impedance, thus can be used to efficiently drive relatively low impedance systems.

The effective transconductance of the HEMT common-source HBT common-emitter 3-terminal composite device as defined in a 2-port network 76 with one terminal coupled to ground, illustrated in FIG. 4, is given in equation (7) below:

$$Gm_{eff} \approx \left\{ \frac{Gm_{HEMT}}{1 + Gm_{HEMT} * r_s} * r_{ds} \right\} \left\{ \frac{\alpha_0}{\frac{r_b}{\beta_0+1} + \frac{1}{Gm_{HBT}} + r_e + R_e} \right\} \quad (7)$$

The input and output impedance of the composite device 76, illustrated in FIG. 4, is given by equations (8) and (9):

$$Z_{in}(s) \approx r_g + r_s + r_i + \frac{1}{s * C_{gs}} \quad (8)$$

$$Z_{out}(s) \approx r_o * (1 + \frac{Gm_{HBT}}{1 + Gm_{HBT} * r_e}) \quad (9)$$

where

$$Gm_{HBT} = \frac{I_c * q}{n * KT} \text{ and } \alpha_0 = \frac{\beta_0}{1 + \beta_0}$$

The transconductance for the HEMT common-source HBT common-collector 3-terminal composite device as defined in a 2-port network with one of its terminals coupled to Ground, illustrated in FIG. 5, is given in equation (10):

$$Gm_{eff} \approx \left\{ \frac{Gm_{HEMT}}{1 + Gm_{HEMT} * r_s} * r_{ds} \right\} \left\{ \frac{1}{\frac{r_b}{\beta_0+1} + \frac{1}{Gm_{HBT}} + r_e + R_L} \right\} \quad (10)$$

The input and output impedance of the composite device 84, illustrated in FIG. 5, is provided in equations (11) and (12)

below:

$$Z_{in}(s) \approx r_g + r_s + r_i + \frac{1}{s * C_{gs}} \quad (11)$$

5

$$Z_{out}(s) \approx (r_e + \frac{1}{Gm_{HBT}} + \frac{r_b + r_{ds}}{\beta_0 + 1}) \quad (12)$$

- 10 The 4-terminal HEMT-HBT topology 48, illustrated in FIG. 1b, can also be configured into 3-terminal composite devices, which can be used for 2-port low noise-high linearity amplifiers or 3-port mixer applications as illustrated in FIGS. 6 and 7, respectively. Using like reference numerals for components with similar function, the HEMT-HBT composite device, illustrated in FIG. 6, generally identified with the reference numeral 90, is configured as a common-source HEMT 50 with a common-base HBT 52. In particular, the source electrode of the HEMT 50 is coupled to ground, as is
 15 the base electrode of the HBT 52, thus eliminating the external terminals 56 and 58, illustrated in FIG. 1b. An external load resistor R_L 92 may be connected between ground and external terminal 94 to define an output load impedance at the output of the resulting 2-port HEMT common-source HBT common-base amplifier 90, as illustrated in FIG. 6.

The composite device 90, illustrated in FIG. 6, combines a common-source HEMT with a common-base HBT to form a hybrid cascode. An important aspect of this configuration is that the device can provide high input and high output impedances simultaneously. The common-source configured HEMT 50 provides optimally low noise figure performance, while the common-base configured HBT 52 provides wideband high linearity. A common advantage of any cascode configuration is that the Miller capacitance multiplication of the input device is reduced. In addition, the low loss HEMT input and HBT output characteristics of the HEMT-HBT cascode illustrated in FIG. 6 allows for the construction of low loss matching networks to tune the input HEMT 50 for noise and the output HBT 52 for linearity and power. The
 25 high input and output impedance provide optimal use of parallel feedback from the collector output of the HBT 52 to the gate input of the HEMT 50. By implementing the HBT 52 in a common-base configuration, the composite device 90 will have relatively low noise-high linearity and high frequency capability, attractive for various known high voltage gain applications.

The effective transconductance of the composite device 90 is provided by equation (13), while the input and output
 30 impedances are provided in equations (14) and (15).

$$Gm_{eff} \approx \left\{ \frac{Gm_{HEMT}}{1 + Gm_{HEMT} * r_s} \right\} * \alpha_0 \quad (13)$$

35

$$Z_{in}(s) \approx r_g + r_s + r_i + \frac{1}{s * C_{gs}} \quad (14)$$

$$Z_{out}(s) \approx (\beta(s) + 1) * r_0 \text{ where } \beta(s) \approx \frac{\beta_0}{1 + s/\omega_T} \quad (15)$$

An alternate configuration of the topology illustrated in FIG. 1b is shown in FIG. 7 and identified with the reference
 45 numeral 96. In this configuration the HEMT 50 is configured as a common source, thus eliminating the external terminal 56. By utilizing the base input of the HBT 52 as a third port, a HEMT-HBT 3-port composite device 96, configured as an active mixer cell, is provided; analogous to a dual-gate FET active mixer. The low noise HEMT gate input 54 is used for the receiver RF port, while the HBT base input may be used as an LO (local oscillator) input port. The HBT collector terminal 60 may be used, for example, to extract out the IF frequency.

Various other MMICs with useful circuit configurations can be derived from the topologies illustrated in FIG. 1. For
 50 example, a common-gate HEMT actively matched HBT Darlington feedback amplifier as illustrated in FIG. 8 can be configured from the composite topology illustrated in FIG. 1a. In addition, a HEMT-HBT low noise amplifier, as illustrated in FIG. 12, can be formed from the device topology illustrated in FIG. 1b.

Referring to FIG. 8, like reference numerals are used to identify components having like functions relative to FIG.
 55 1a. The configuration illustrated in FIG. 8 is useful as a common-gate HEMT actively matched HBT Darlington feedback amplifier. The amplifier, generally identified with the reference numeral 98, includes a HEMT 22 and an HBT 24 configured in the topology as illustrated in FIG. 1a. In addition, the amplifier 98 includes a second HBT Q₂ 100 connected to the first HBT Q₁ 24 to form a Darlington pair. A feedback resistor R_f₀ 102 is connected between the collectors of the Darlington pair and the drain of a HEMT M₁ 22. A biasing resistor R_{bias} 104 is connected between the base of the HBT Q₂ 100 and ground, while an emitter resistor R_{ee} 106 is connected between the emitter terminal of the HBT Q₂ 100 and

ground. The amplifier 98 output is available at an output terminal 108, connected to the collector electrodes of the Darlington pair HBTs Q₁, Q₂ 24, 100 by way of an output resistor R_{out} 110. A third external terminal 112 is available for connection of an external power supply VCC to the circuit by way of a load resistor R_{load} 114. The HEMT M₁ 22 is configured as a common-gate. A source terminal is connected to an external terminal 26, which forms the input of the amplifier 98. The common-gate HEMT M₁ 22 provides active input matching, which can be electrically tuned for optimum return loss and noise figure performance while providing relatively good RF impedance matching without the use of large, cumbersome microstrip matching components. By employing the active input match, the HBT Darlington feedback network can be independently adjusted for IP3 and gain performance without compromising the input match. As shown in FIGS. 9, 10 and 11, the amplifier 98 has a gain of > 10 dB over a frequency range from dc-5 GHz; a minimum noise figure < 4 dB and an IP3 as great as 29 dBm with excellent input return loss. Referring to FIG. 9, which illustrates the gain as a function of HEMT bias values at a specific bias of V_{gs} equal to -0.8 v and I_{ds} = 2.6 mA, the transconductance G_m of the amplifier 98 is about 20 mS, which corresponds to an input impedance of about 50 Ω, calculated from equation (2) above.

FIG. 10 is a graphical illustration of the noise figure performance as a function of frequency for various active HEMT bias values. As shown, the noise figure performance is highly dependent on the active HEMT bias. For example, as shown, high bias values result in lower noise figures. However, at higher bias values the input return loss gets worse. By choosing a smaller HEMT device, both low noise figure performance, as well as good input return loss performance, can be achieved simultaneously.

FIG. 11 is a graphical illustration of the linearity or IP3 performance of the amplifier 98 as a function of frequency for various HEMT active bias conditions. As shown, the amplifier 98 has a maximum IP3 of 29 dBm at 1 GHz, which could not be achieved for the same total current consumption (DC power) using HEMT devices alone.

FIG. 12 illustrates another useful circuit configuration based on the topologies illustrated in FIG. 1. In particular, FIG. 12 is a schematic diagram of a common source HEMT-HBT low noise amplifier, generally identified with the reference numeral 116, based upon the HEMT-HBT topology illustrated in FIG. 1a. In FIG. 12 like reference numerals are used to identify components with like functions relative to FIG. 1a. The gate terminal of the HEMT M₁ 36 is connected to the external terminal 40, forming an RF input RFin. The HEMT M₁ 36 is configured as a common source HEMT. As such, the source terminal of the HEMT M₁ 36 is connected to ground by way of a parallel connected source resistor R_{ss} 118 and a source capacitor C_{ss} 120. A first feedback resistor Rf₁ 122 is connected between the collector of the HBT Q₁ 38 and the drain of the HEMT M₁ 36. A second feedback resistor Rf₂ is connected between the emitter of the HBT Q₁ 38 and the gate of the HEMT M₁ 36 forming a HEMT low noise input stage.

A second HBT Q₂ 122 is connected to the HBT Q₁ 38 to form a Darlington pair. A biasing resistor R_{bias} 124 is connected between the base of the HBT Q₂ 122 and ground, while an emitter resistor R_{ee} 126 is connected between the emitter terminal of the HBT Q₂ 122 and ground. An RF_{out} terminal is available at an external terminal 128, connected to the collectors of the HBTs Q₁, Q₂ 38, 122 by way of an output resistor R_{out} 130. A supply voltage V_{cc} is connected to the collectors of the Darlington pair by way of a load resistor R_{load} 132.

The performance of the amplifier 116 is based upon a 0.2 x 200 μm² pseudomorphic InGaAs-GaAs HEMT device nominally biased to 14 mA. As shown in FIGS. 13 and 14, the HEMT M₁ 36 provides relatively low noise figure performance and a gain of about 10 dB to reduce the high noise figure of the HBT Darlington stage. The common source HEMT M₁ 36 is directly coupled to the HBT Darlington stage to accommodate self-biasing of the HEMT M₁ 36. The feedback resistors Rf₁ and Rf₂, load resistor R_{load} and DC bias resistor R_{ss} are used to set up the self-biasing of the HEMT M₁ 36. The Darlington stage is formed from the HBTs Q₁, Q₂ 38, 122, the Rf feedback resistor Rf₁, the series feedback resistor R_{ee} and the bias resistor R_{bias}. The HBTs Q₁, Q₂ 38, 122 may be formed as 2 x 10 μm² four-finger AlGaAs-GaAs HBT devices, both biased with 13 mA of collector current. The resistor R_{out} provides good output return loss match. The amplifier 116 is self-biased through the external power supply VCC, which may be 12 volts and draws about 40 mA of current.

The gain and return loss of the amplifier 116 is illustrated in FIG. 13. As shown, the amplifier 116 achieves a nominal gain of 21 dB with a bandwidth from 1-8 GHz. The input-return loss is better than 12 dB, while the output-return loss is better than 20 dB through most of the band. FIG. 14 illustrates the noise figure as well as the IP3 performance of the amplifier 116. As shown, the noise figure performance is < 2.6 dB in the 2-5.5 GHz range, between 2.6 and 2.8 dB from the 6-9.5 GHz range, and 3 dB at 10 GHz. The IP3 or linearity performance is between 14-16 dBm from 1-6 GHz and then increases to about 18 dBm at 10 GHz.

FIG. 15 is a graphical illustration of the gain and output power as a function of the input power of the amplifier 116 at midband. As shown, the measured saturated output power is > 12 dBm at midline. Compared to HBT single-technology Darlington amplifier, the HEMT-HBT Darlington amplifier has better performance capabilities compared to the HBT single-technology Darlington amplifier implementation which achieved 11 dB nominal gain, 10 GHz bandwidth, and 5-6.5 dB noise figure, the low noise HEMT-HBT direct coupled amplifier 116 achieves > 2 dB improvement in the noise figure and a 10 dB increase in the gain without significantly compromising the bandwidth or output power capability.

Each of the devices disclosed above may be formed as a monolithic microwave integrated circuit (MMIC). As discussed above, each of the circuits may be derived from one of the topologies illustrated in FIG. 1 and includes mono-

lithically integrated HEMTs and HBTs. The devices disclosed herein can be fabricated by known methods as disclosed in "Monolithic HEMT-HBT Integration by Selective MBE," by D.C. Streit, D.K. Umemoto, K.W. Kobayashi and A.K. Oki, IEEE Transactions on Electron Devices, Vol. 42, No. 4, April 1995, pp. 618-623; "A Monolithic HBT-Regulated HEMT LNA by Selective MBE," by D.C. Streit, K.W. Kobayashi, A.K. Oki and D.K. Umemoto, Microwave and Guided Wave Letts., Vol. 5, No. 4, April 1995, pp. 124-126; U.S. Patent Application Serial No. 08/333,538, filed on November 2, 1994 all herein incorporated by reference. In addition to the HEMT-HBTs, the devices, as shown in the schematic drawings, include thin-film resistors (TFR) and metal-insulator-metal (MIM) capacitors, also known in the art. The amplifier 116, illustrated in FIG. 12, can be fabricated in an MMIC package, measuring 0.9 x 0.7 mm².

Obviously, many modifications and variations of the present invention are possible in light of the above teachings.

Thus, it is to be understood that, within the scope of the appended claims, the invention may be practiced otherwise than as specifically described above.

What is claimed and desired to be secured by Letters Patent of the United States is:

Claims

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1. A monolithic microwave integrated composite device (MMIC) topology comprising:

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a high electron mobility transistor (HEMT) having gate, source and drain terminals; and
a heterojunction bipolar transistor (HBT) having base collector and emitter terminals, said base terminal connected to said drain terminal of said HEMT.

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2. An MMIC topology as recited in claim 1, wherein said gate terminal of said HEMT is electrically coupled to a terminal for connection to an external circuit, and/or

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wherein said source terminal of said HEMT is electrically coupled to a terminal for connection to an external circuit, and/or
wherein said collector terminal of said HBT is electrically coupled to a terminal for connection to an external circuit, and/or
wherein said emitter terminal of said HBT is electrically coupled to a terminal for connection to an external circuit.

3. A monolithic microwave integrated circuit (MMIC) topology comprising:

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a high electron mobility transistor (HEMT) having gate, drain and source terminals; and
a heterojunction bipolar junction transistor (HBT) having base collector and emitter terminals, said emitter terminal of said HBT being electrically coupled to said drain terminal of said HEMT.

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4. An MMIC topology as recited in claim 3, wherein said gate terminal of said HEMT is electrically coupled to a terminal for connection to an external electrical circuit, and/or

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wherein said source terminal of said HEMT is electrically coupled to a terminal for connection to an external circuit, and/or
wherein said base terminal of said HBT is electrically coupled to a terminal for connection to an external electrical circuit, and/or
wherein said collector terminal is electrically coupled to a terminal for connection to an external electrical circuit.

5. A monolithic microwave integrated circuit (MMIC) amplifier comprising:

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a high electron mobility transistor (HEMT) having gate, drain and source terminals, said gate terminal of said HEMT electrically coupled to ground; and
a heterojunction bipolar transistor (HBT) having base, collector and emitter terminals, said base terminal of said HBT being electrically coupled to said drain terminal of said HEMT, said emitter terminal being electrically coupled to ground, wherein said source terminal of said HEMT and said collector terminal of said HBT are each electrically coupled to a terminal for connection to an external electrical circuit.

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6. An MMIC as recited in claim 5, further including a first resistor, said resistor electrically coupled between said emitter terminal of said HBT and ground.

7. A monolithic microwave integrated circuit (MMIC) amplifier comprising:

a high electron mobility transistor (HEMT) having gate, drain and source terminals, said gate terminal of said HEMT electrically coupled to ground; and

5 a heterojunction bipolar transistor (HBT) having base, collector and emitter terminals, said base terminal of said HBT being electrically coupled to said drain terminal of said HEMT, said collector terminal being electrically coupled to ground, wherein said source terminal of said HEMT and said emitter terminal of said HBT are each electrically coupled to a terminal for connection to an external electrical circuit.

10 8. A monolithic microwave integrated circuit (MMIC) amplifier comprising:

a high electron mobility transistor (HEMT) having gate, drain and source terminals, said source terminal of said HEMT electrically coupled to ground; and

15 a heterojunction bipolar transistor (HBT) having base, collector and emitter terminals, said base terminal of said HBT being electrically coupled to said drain terminal of said HEMT, said emitter terminal being electrically coupled to ground, wherein said gate terminal of said HEMT and said collector terminal of said HBT are each electrically coupled to a terminal for connection to an external electrical circuit.

20 9. An MMIC as recited in claim 8, further including a first resistor, said resistor electrically coupled between said emitter terminal of said HBT and ground.

10. A monolithic microwave integrated circuit (MMIC) amplifier comprising:

25 a high electron mobility transistor (HEMT) having gate, drain and source terminals, said source terminal of said HEMT electrically coupled to ground; and

a heterojunction bipolar transistor (HBT) having base, collector and emitter terminals, said base terminals of said HBT being electrically coupled to said drain terminal for said HEMT, said collector terminal being electrically coupled to ground, wherein said gate terminal of said HEMT and said emitter terminal of HBT are each electrically coupled to a terminal for connection to an external electrical circuit.

30 11. A monolithic microwave integrated circuit (MMIC) amplifier comprising:

a high electron mobility transistor (HEMT) having gate, drain and source terminals, said source terminal of said HEMT electrically coupled to ground; and

35 a heterojunction bipolar transistor (HBT) having base, collector and emitter terminals, said emitter terminal of said HBT being electrically coupled to said drain terminal of said HEMT, said base terminal being electrically coupled to ground, wherein said gate terminal of said HEMT and said collector terminal of said HBT are each electrically coupled to a terminal for connection to an external electrical circuit.

40 12. A monolithic microwave integrated circuit (MMIC) mixer comprising:

a high electron mobility transistor (HEMT) having gate, drain and source terminals, said source terminal of said HEMT electrically coupled to ground; and

45 a heterojunction bipolar transistor (HBT) having base, collector and emitter terminals, said emitter terminals of said HBT being electrically coupled to said drain terminal of said HEMT, wherein said gate terminal of said HEMT and said base and collector terminals of said HBT are each electrically coupled to a terminal for connection to an external electrical circuit.

50 13. A monolithic microwave integrated circuit (MMIC) amplifier comprising:

a high electron mobility transistor (HEMT) having gate, drain and source terminals, said gate terminal of said HEMT electrically coupled to ground; and

55 a first heterojunction bipolar transistor (HBT) having first base, first collector and first emitter terminals, said first base terminal of said HBT being electrically coupled to said drain terminal of said HEMT, said source terminal being electrically coupled to a terminal forming an amplifier input for connection to an external circuit; a second HBT having base, collector and emitter terminals, said second HBT having second base, second collector and second emitter terminals, said second HBT being electrically coupled to said first HBT to form a Darlington pair;

an output terminal electrically coupled to said first and said collector terminals for connection to an external

electrical circuit; and
a supply terminal electrically coupled to said first and second collector terminals for connection to an external supply voltage.

- 5 14. An MMIC as recited in claim 13, further including a first resistor, electrically coupled between said first and said second collector terminals and said drain terminal of said HEMT, and/or

a second resistor, electrically coupled between said second base terminal and ground, and/or
a third resistor, electrically coupled between said second emitter and ground, and/or
10 a fourth resistor, electrically coupled between said output terminal and said first and second collectors, and/or
a fifth resistor, electrically coupled between said first and second collector terminals and said supply terminal.

15. A monolithic microwave integrated circuit (MMIC) comprising:

15 a high electron mobility transistor having gate, drain and source terminals, said source terminal being electrically coupled to ground, said gate terminal being electrically coupled to an input terminal for connection to an external circuit forming an amplifier input;
a first heterojunction bipolar transistor (HBT) having first base, first collector and first emitter terminals, said first base terminal being electrically coupled to said drain terminal of said HEMT;
20 a second HBT having second base, second collector and second emitter terminals, electrically coupled to said first HBT forming a Darlington pair;
an output terminal, electrically coupled to said first and second collector terminals for connection to an external circuit; and
a supply terminal electrically coupled to a supply terminal for connection to an external voltage supply.

- 25 16. An MMIC as recited in claim 15, further including a first resistor, electrically coupled between said first and second collector terminals and said drain terminal of said HEMT, and/or

30 a second resistor, electrically coupled between said first and second collector terminals and said drain terminal of said HEMT, and/or
a second resistor, electrically coupled between said second base terminal and ground, and/or
a third resistor, electrically coupled between said second emitter terminal and ground, and/or
a fourth resistor electrically coupled between said output terminal and said first and second collector terminals, and/or
35 a fifth resistor, electrically coupled between said supply terminal and said first and second collector terminals, and/or
a sixth resistor, electrically coupled between said source terminal and ground, and/or
a capacitor, electrically coupled between said source terminal and ground, and/or
a seventh resistor, electrically coupled between said first emitter terminal and said source terminal.

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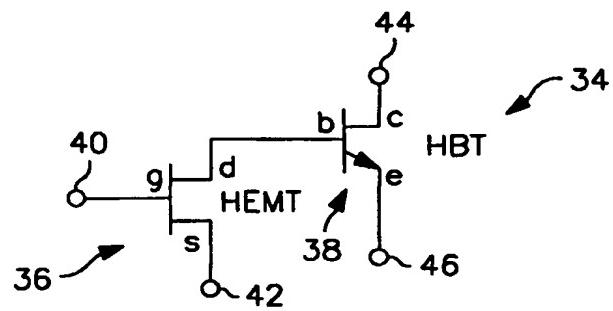


FIG. IA

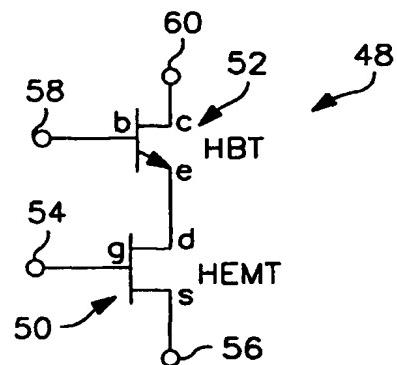


FIG. IB

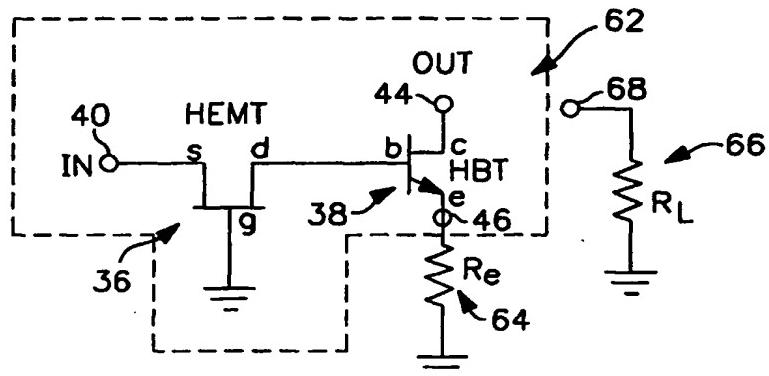


FIG. 2

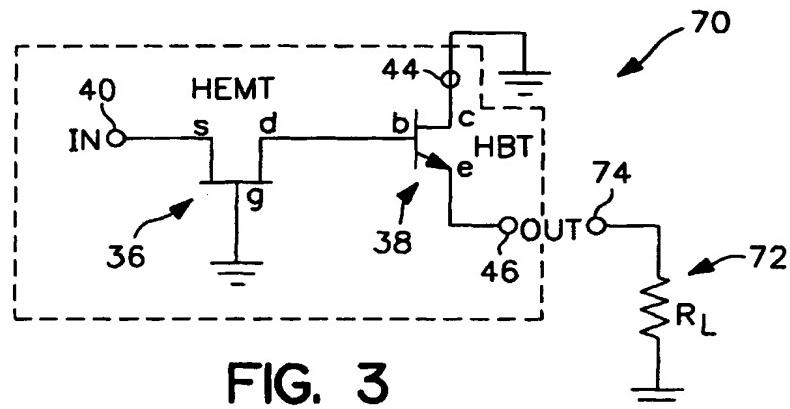


FIG. 3

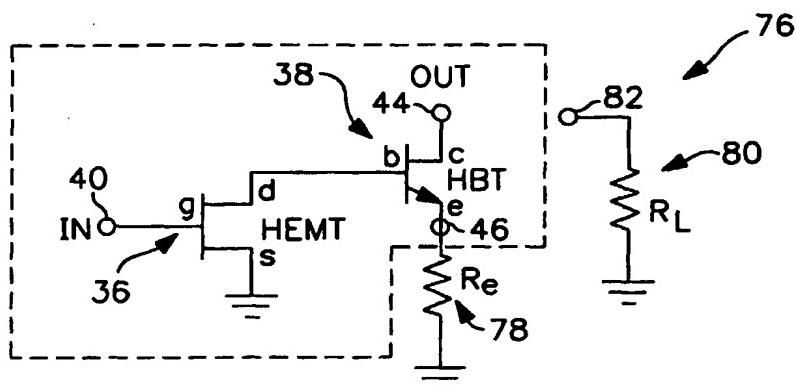
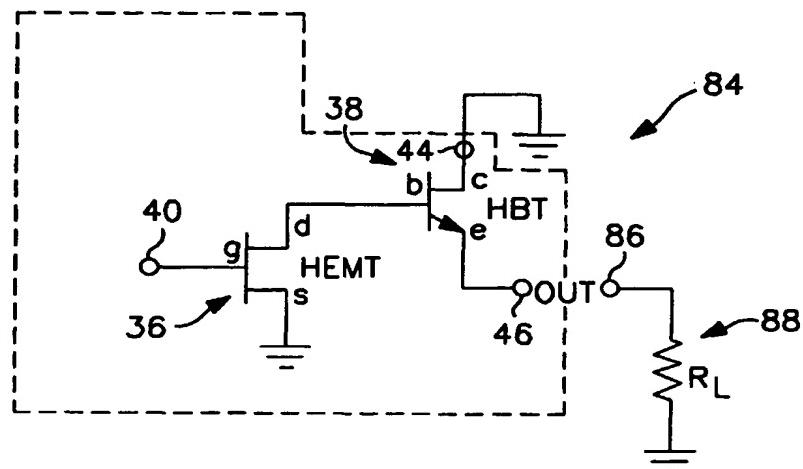
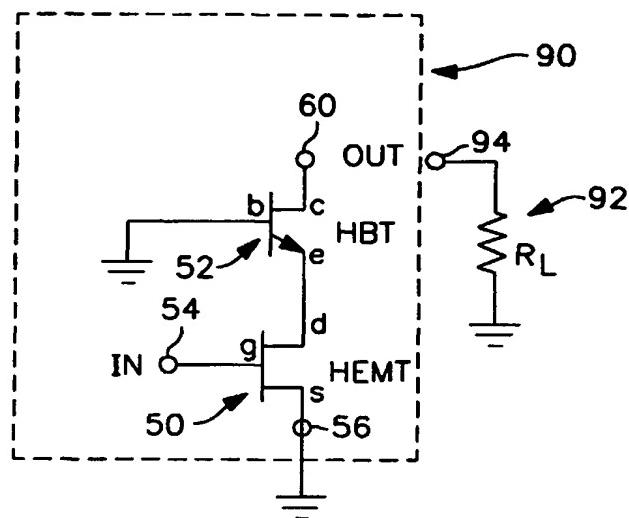
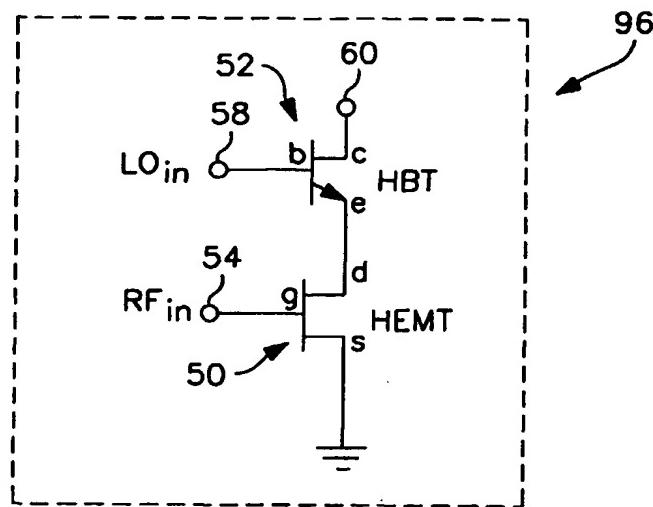


FIG. 4

FIG. 5**FIG. 6****FIG. 7**

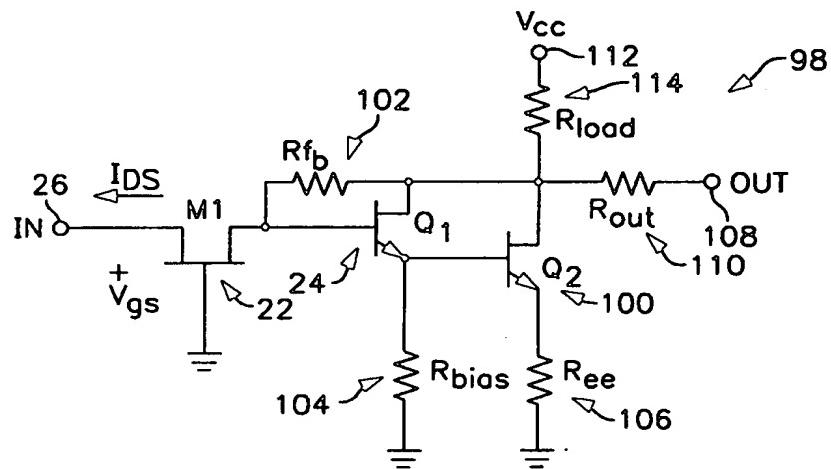


FIG. 8

Vgs	Ids	Vgs	Ids
-0.55 V	12 mA	-0.7 V	5.25 mA
-0.6 V	9.5 mA	-0.75 V	3.8 mA
-0.065 V	7.25 mA	-0.8 V	2.6 mA

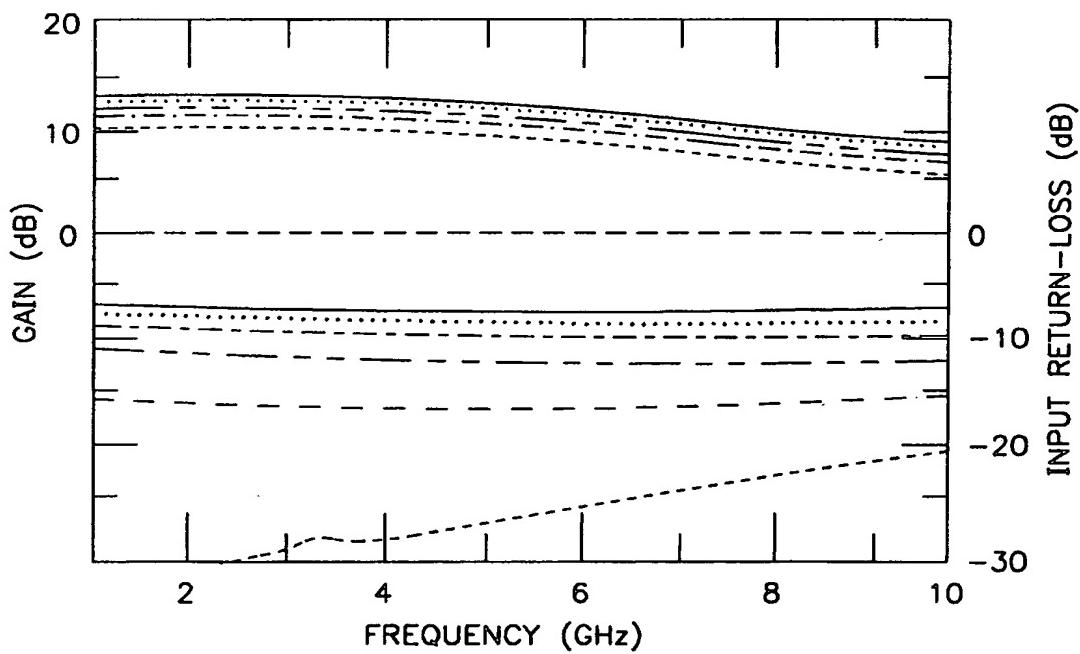


FIG. 9

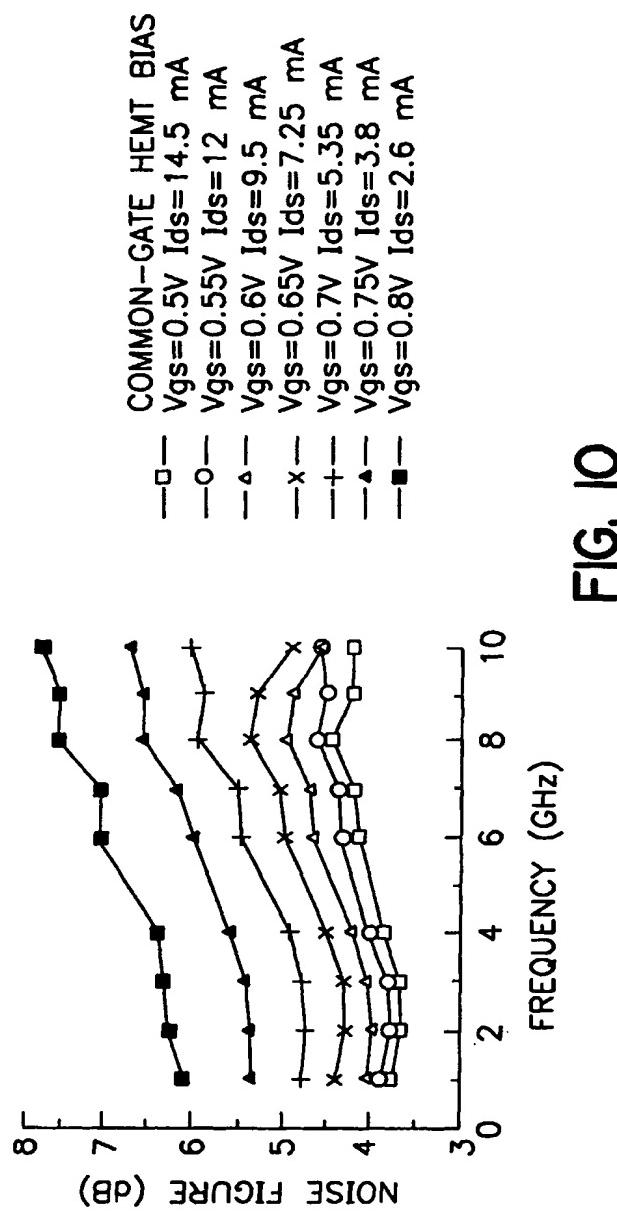


FIG. 10

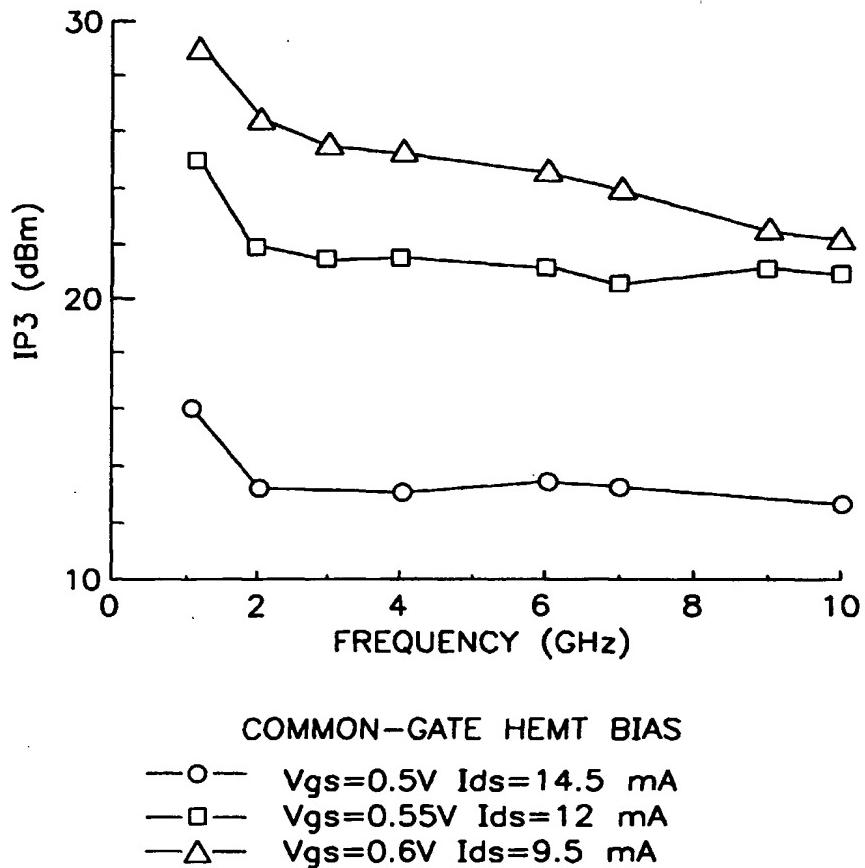


FIG. II

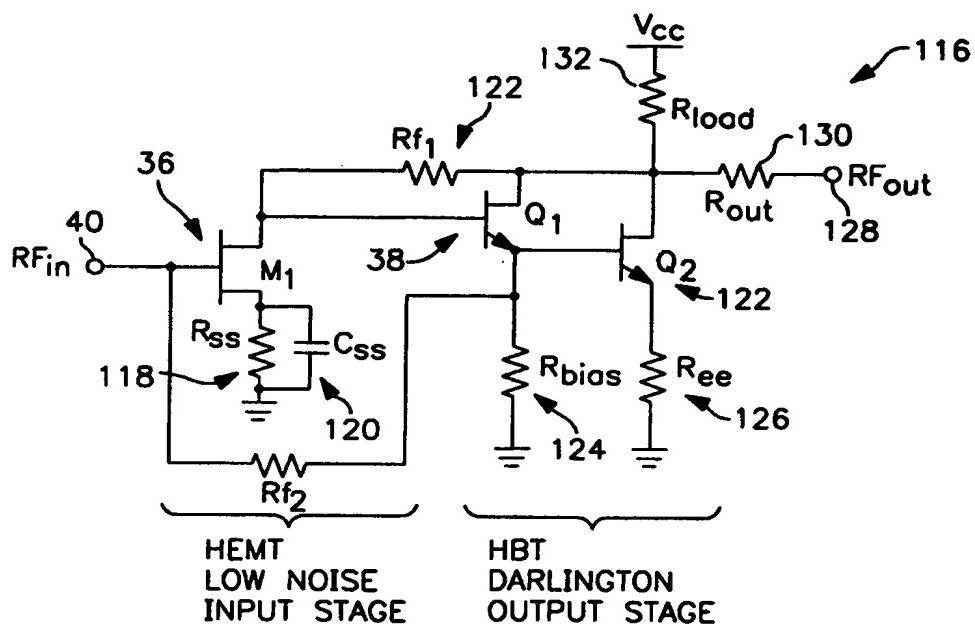


FIG. 12

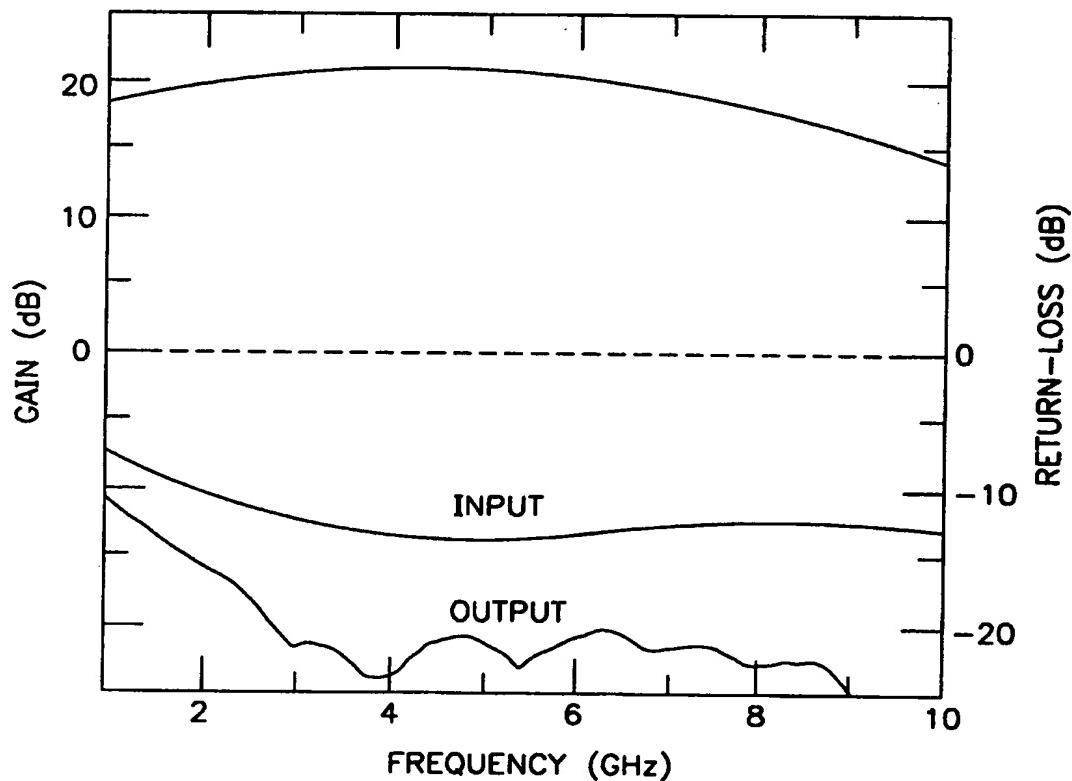


FIG. 13

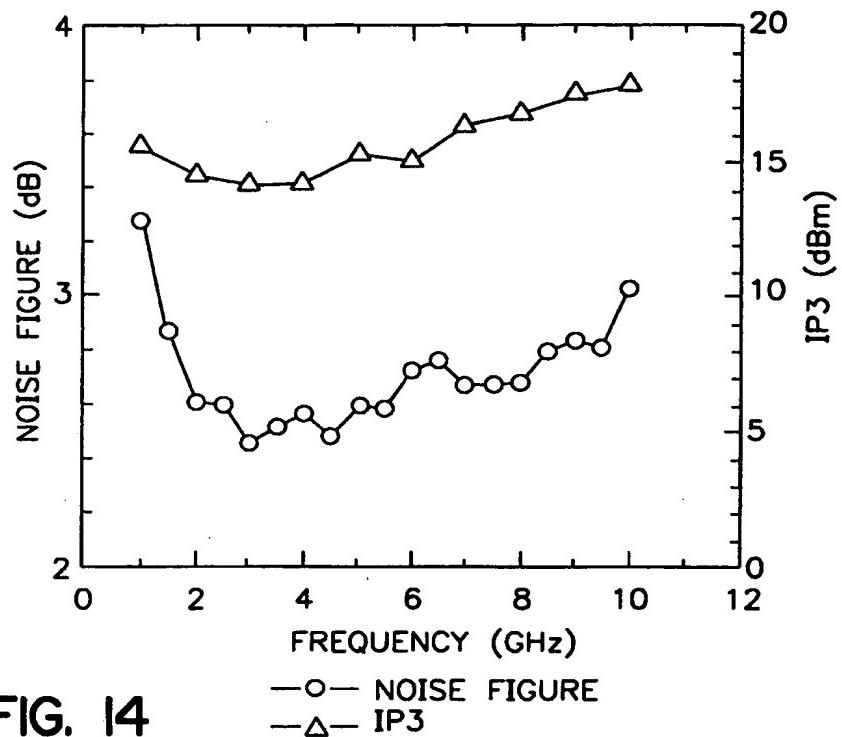


FIG. 14

—○— NOISE FIGURE
—△— IP₃

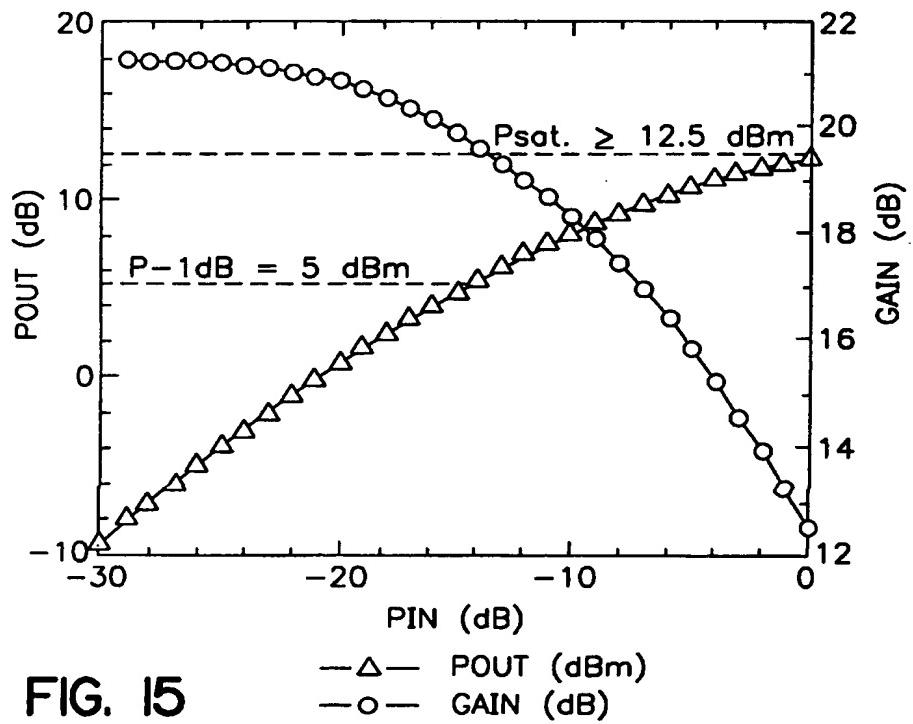


FIG. 15

—△— POUT (dBm)
—○— GAIN (dB)



EUROPEAN SEARCH REPORT

Application Number
EP 97 10 0525

DOCUMENTS CONSIDERED TO BE RELEVANT					
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.)		
Y	US 4 553 108 A (YOUNG JAMES P) 12 November 1985 * column 1, line 13 - line 26; figure 1 * * column 2, line 29 - line 52 * ---	1,3,5,7, 8,10,11	H03F3/193		
Y	US 5 086 282 A (AINA OLALEYE A ET AL) 4 February 1992 * column 2, line 47 - line 60; figure 1 * ---	1,3,5,7, 8,10,11			
Y,D	IEEE MICROWAVE AND GUIDED WAVE LETTERS, vol. 6, no. 1, 1 January 1996, pages 55-57, XP000547031 KOBAYASHI K W ET AL: "A MONOLITHIC HEMT-HBT DIRECT-COUPLED AMPLIFIER WITH ACTIVE INPUT MATCHING" * page 56; figure 1 * ---	1,3,5,7, 8,10,11			
A	PROCEEDINGS OF THE GALLIUM ARSENIDE INTEGRATED CIRCUITS SYMPOSIUM (GAAS IC), SAN JOSE, OCT. 10 - 13, 1993, no. SYMP. 15, 10 October 1993, INSTITUTE OF ELECTRICAL AND ELECTRONICS ENGINEERS, pages 211-214, XP000462975 CHANG K W ET AL: "A V-BAND MONOLITHIC INP HEMT DOWNCONVERTER" * the whole document *	12	TECHNICAL FIELDS SEARCHED (Int.Cl.)		
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Y	US 5 398 004 A (KOBAYASHI KEVIN W) 14 March 1995 * column 3, line 25 - column 5, line 10; figure 1 * ---	13,15 -/-			
The present search report has been drawn up for all claims					
Place of search	Date of completion of the search	Examiner			
BERLIN	18 June 1997	Breusing, J			
CATEGORY OF CITED DOCUMENTS					
X : particularly relevant if taken alone	T : theory or principle underlying the invention				
Y : particularly relevant if combined with another document of the same category	E : earlier patent document, but published on, or after the filing date				
A : technological background	D : document cited in the application				
O : non-written disclosure	L : document cited for other reasons				
P : intermediate document	A : member of the same patent family, corresponding document				



European Patent
Office

EUROPEAN SEARCH REPORT

Application Number
EP 97 10 0525

DOCUMENTS CONSIDERED TO BE RELEVANT			CLASSIFICATION OF THE APPLICATION (Int.Cl.)
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	
Y	IEEE MICROWAVE AND GUIDED WAVE LETTERS, vol. 5, no. 12, December 1995, NEW YORK, US, pages 442-444, XP000539157 K. W. KOBAYASHI ET AL: "A NOVEL MONOLITHIC LNA INTEGRATING A COMMON-SOURCE HEMT WITH AN HBT DARLINGTON AMPLIFIER" * page 443; figure 1 *	13,15	
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A	US 5 387 880 A (KOBAYASHI KEVIN W) 7 February 1995 * abstract; figure 1 *	1	
A,D, P	EP 0 710 984 A (TRW INC) 8 May 1996 * claims 1,9,10,12 *	1	
A	EP 0 643 496 A (SIEMENS AG) 15 March 1995 * claim 3; figure 2 *	-----	TECHNICAL FIELDS SEARCHED (Int.Cl.)
The present search report has been drawn up for all claims			
Place of search	Date of completion of the search	Examiner	
BERLIN	18 June 1997	Breusing, J	
CATEGORY OF CITED DOCUMENTS		T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document	
X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document			